## Amendments to the Specification

In the Title:

Please replace the title with the following:

PROCESS FOR PRODUCING LOW DEFECT DENSITY SILICON.

IN THE ABSTRACT:

Please replace text of the abstract on page 52 with the following:

The present invention relates to a process for preparing a single crystal silicon, which contains an axially symmetric region which is free of agglomerated intrinsic point defects. The process for preparing the single crystal silicon includes controlling the ratio $v/G_0$ and the cooling rate of the crystal from a solidification temperature to about 1,050 °C, in order to cause the formation of an axially symmetrical segment which is substantially free of agglomerated intrinsic point defects. During a portion of the process, the ingot is grown at a pull rate in the range of from 0.2 mm/min to 0.8 mm/min.